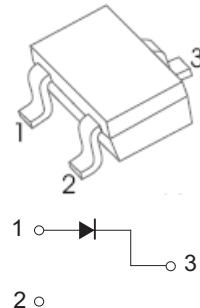




## SOT-323 Plastic-Encapsulate Diodes

**MMBD4148W/BAS16W**

SWITCHING DIODE

**SOT-323****FEATURES**

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

**MARKING: A2****Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C**

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V <sub>RM</sub>	100	V
Peak Repetitive Peak Reverse Voltage	V <sub>RRM</sub>		
Working Peak Reverse Voltage	V <sub>RWM</sub>	75	V
DC Blocking Voltage	V <sub>R</sub>		
RMS Reverse Voltage	V <sub>R(RMS)</sub>	53	V
Forward Continuous Current	I <sub>FM</sub>	300	mA
Average Rectified Output Current	I <sub>O</sub>	150	mA
Peak Forward Surge Current @t=1.0μs @t=1.0s	I <sub>FSM</sub>	2.0 1.0	A
Power Dissipation	P <sub>D</sub>	200	mW
Thermal Resistance Junction to Ambient	R <sub>θJA</sub>	625	°C/W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55~+150	°C

**ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	V <sub>(BR)</sub>	I <sub>R</sub> = 10μA	75		V
Reverse voltage leakage current	I <sub>R</sub>	V <sub>R</sub> =75V V <sub>R</sub> =20V		1 25	μA nA
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =1mA I <sub>F</sub> =10mA I <sub>F</sub> =50mA I <sub>F</sub> =150mA		0.715 0.855 1 1.25	V
Diode capacitance	C <sub>D</sub>	V <sub>R</sub> =0, f=1MHz		2	pF
Reveres recovery time	t <sub>rr</sub>	I <sub>F</sub> =I <sub>R</sub> =10mA, I <sub>rr</sub> =0.1×I <sub>R</sub> , R <sub>L</sub> =100Ω		4	ns